Sakari Sintonen

List of Publications by Year
in descending order

32	698	623188 14	552369 26
papers	citations	h-index	g-index

32	32	32	1139
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Aluminum oxide from trimethylaluminum and water by atomic layer deposition: The temperature dependence of residual stress, elastic modulus, hardness and adhesion. Thin Solid Films, 2014, 552, 124-135.	0.8	155
2	Thermal and plasma enhanced atomic layer deposition of SiO2 using commercial silicon precursors. Thin Solid Films, 2014, 558, 93-98.	0.8	66
3	Preparation of deep UV transparent AlN substrates with high structural perfection for optoelectronic devices. CrystEngComm, 2016, 18, 3488-3497.	1.3	62
4	Defects in Single Crystalline Ammonothermal Gallium Nitride. Advanced Electronic Materials, 2017, 3, 1600496.	2.6	40
5	Aluminum oxide/titanium dioxide nanolaminates grown by atomic layer deposition: Growth and mechanical properties. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	0.9	38
6	Synchrotron radiation x-ray topography and defect selective etching analysis of threading dislocations in GaN. Journal of Applied Physics, 2014, 116, 083504.	1.1	37
7	Diamond-like carbon (DLC) thin film bioelectrodes: Effect of thermal post-treatments and the use of Ti adhesion layer. Materials Science and Engineering C, 2014, 34, 446-454.	3.8	30
8	X-ray reflectivity characterization of atomic layer deposition Al2O3/TiO2 nanolaminates with ultrathin bilayers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, .	0.9	28
9	Thermal conductivity of amorphous Al₂O₃/TiO₂nanolaminates deposited by atomic layer deposition. Nanotechnology, 2016, 27, 445704.	1.3	27
10	Microscratch testing method for systematic evaluation of the adhesion of atomic layer deposited thin films on silicon. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	0.9	21
11	Large-area analysis of dislocations in ammonothermal GaN by synchrotron radiation X-ray topography. Applied Physics Express, 2014, 7, 091003.	1.1	20
12	Incorporation and effects of impurities in different growth zones within basic ammonothermal GaN. Journal of Crystal Growth, 2016, 456, 43-50.	0.7	20
13	Effect of growth temperature on the epitaxial growth of ZnO on GaN by ALD. Journal of Crystal Growth, 2014, 398, 18-22.	0.7	19
14	Mechanical and optical properties of as-grown and thermally annealed titanium dioxide from titanium tetrachloride and water by atomic layer deposition. Thin Solid Films, 2021, 732, 138758.	0.8	17
15	Analysis of threading dislocations in void shape controlled GaN re-grown on hexagonally patterned mask-less GaN. Journal of Crystal Growth, 2012, 344, 59-64.	0.7	14
16	Defect structure of a free standing GaN wafer grown by the ammonothermal method. Journal of Crystal Growth, 2014, 406, 72-77.	0.7	13
17	Nanotribological, nanomechanical and interfacial characterization of atomic layer deposited TiO2 on a silicon substrate. Wear, 2015, 342-343, 270-278.	1.5	13
18	Evolution of impurity incorporation during ammonothermal growth of GaN. Journal of Crystal Growth, 2016, 456, 51-57.	0.7	13

#	Article	IF	Citations
19	Patterning of sapphire/GaN substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1509-1512.	0.8	11
20	An investigation of structural properties of GaN films grown on patterned sapphire substrates by MOVPE. Physica B: Condensed Matter, 2009, 404, 4911-4915.	1.3	8
21	Synchrotron radiation Xâ€ray topography and Xâ€ray diffraction of homoepitaxial GaN grown on ammonothermal GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1630-1632.	0.8	7
22	Tribological properties of thin films made by atomic layer deposition sliding against silicon. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	0.9	7
23	Evaluation of critical thickness of GaP0.98N0.02 layer on GaP substrate by synchrotron X-ray diffraction topography. Thin Solid Films, 2013, 534, 680-684.	0.8	5
24	Top-seeded solution growth of SrTiO 3 single crystals virtually free of mosaicity. Journal of Crystal Growth, 2017, 468, 305-310.	0.7	5
25	Characterization of InGaN/GaN and AlGaN/GaN superlattices by X-ray diffraction and X-ray reflectivity measurements. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1790-1793.	0.8	4
26	MOCVD growth and characterization of nearâ€surface InGaN/GaN single quantum wells for nonâ€radiative coupling of optical excitations. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1667-1669.	0.8	4
27	Synchrotron radiation X-ray topography and defect selective etching analysis of threading dislocations in halide vapor phase epitaxy GaN crystal grown on ammonothermal seed. Japanese Journal of Applied Physics, 2019, 58, SCCB19.	0.8	4
28	Xâ€ray diffraction study of GaN grown on patterned substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1524-1527.	0.8	2
29	Effect of GaN cap thickness on carrier dynamics in InGaN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 727-729.	0.8	2
30	Fabrication of GaN structures with embedded network of voids using pillar patterned GaN templates. Journal of Crystal Growth, 2013, 370, 42-45.	0.7	2
31	Analysis of Dislocations Generated during Metalâ€“Organic Vapor Phase Epitaxy of GaN on Patterned Templates. Japanese Journal of Applied Physics, 2013, 52, 01AF01.	0.8	2
32	Synchrotron X-ray diffraction topography study of bonding-induced strain in silicon-on-insulator wafers. Thin Solid Films, 2016, 603, 435-440.	0.8	2